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	Application No.	Applicant(s)	
A	10/665,595	5 THIBEAULT ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Remmon R. Fordé	2826	
The MAILING DATE of this communication apper All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate communication is subsection in Subsection	this application. If not included nication will be mailed in due course	
1. This communication is responsive to <u>2/23/04</u> .			
2. A The allowed claim(s) is/are 37-40 (respectively renumbered	<u>d as 1-4)</u> .		
3. The drawings filed on <u>17 September 2003</u> are accepted by	the Examiner.		
<ul> <li>4. ☐ Acknowledgment is made of a claim for foreign priority una) ☐ All b) ☐ Some* c) ☐ None of the:</li> <li>1. ☐ Certified copies of the priority documents have</li> <li>2. ☐ Certified copies of the priority documents have</li> <li>3. ☐ Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul>	been received. been received in Application	ı No	om the
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the requirem	ents
5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give			OF
6. ☐ CORRECTED DRAWINGS ( as "replacement sheets") mus  (a) ☐ including changes required by the Notice of Draftspers  1) ☐ hereto or 2) ☐ to Paper No./Mail Date  (b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	on's Patent Drawing Review		
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in t			of
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MATE	RIAL must be submitted. Note th	e
<ul> <li>Attachment(s)</li> <li>1. ☑ Notice of References Cited (PTO-892)</li> <li>2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)</li> <li>3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 2/05/04;2/23/04</li> </ul>	6. Interview Sui Paper No./N	ormal Patent Application (PTO-152) mmary (PTO-413), //ail Date Amendment/Comment	
4.   Examiner's Comment Regarding Requirement for Deposit		Statement of Reasons for Allowance	
of Biological Material	9.		Jan 1
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U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04) Application/Control Number: 10/665,595

Art Unit: 2826

## **DETAILED ACTION**

## Reasons For Allowance

Claims 37-40 are allowed.

The following is an examiner's statement of reasons for allowance:

Claim 37 recites a method for growing a light emitting diode structure having an internal disperser layer including the specific method steps of growing a first semiconductor layer on the substrate, the first layer having a rough surface; stopping growth of the semiconductor layer; growing a disperser layer of semiconductor material on the roughened layer, the disperser layer having a different index of refraction than the first layer; growing a second layer on the disperser layer, the second layer having a similar index of refraction as the first layer. The abovementioned specific method steps are neither anticipated by nor obvious over the prior art of record. Likewise, claims 38 and 39 are also allowable as being dependent upon allowable claim 37.

Claim 40 recites a method for manufacturing an AlInGaN light emitting diode having an internal disperser layer including the specific method steps of growing uncoalesced islands of material made of Al<sub>x</sub>In<sub>y</sub>Ga<sub>l-x-y</sub>N, 0≤x≤1, 0≤y≤1, on said substrate; stopping the growth of islands; depositing a disperser layer on said uncoalesced islands, said disperser layer having a different index of refraction from said highly doped GaN material; growing a layer of material made of Al<sub>x</sub>In<sub>y</sub>Ga<sub>l-x-y</sub>N, 0≤x≤1, 0≤y≤1, on said disperser layer, said layer having a smooth surface. The abovementioned specific method steps are neither anticipated by nor obvious over the prior art of record.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## Relevant Prior Art

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Tarsa et al., Hosoba and Krames et al. each disclose methods for making LED structures.

## **Contact Information**

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Remmon R. Fordé whose telephone number is (571) 272-1916. The examiner can normally be reached on Monday-Thursday (8:00-6:30).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J. Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 10/665,595 Page 4

Art Unit: 2826

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Remmon R. Fordé